Resonant Spin-Dependent Tunneling Through Metallic Quantum Well States

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Magneto-transport in spin-valve



Detect decrease in resistance when moments in two ferromagnetic layers are aligned







Spin-dependent tunneling



Quantum size effect in magnetic tunnel junctions with ultrathin Fe(001) electrodes

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FIG. 2. Bias voltage at which the differential conductivity shows maxima, shown as a function of electrode thickness. MTJs with an electrode thicker than 6 ML show two maxima.



Choices of Resonant Tunnel Junctions



Nonmagnetic QW layer

- Long MFP
- QW states cannot be switched

Amorphous barrier layer

- Wider selection of electrodes
- All states tunnel with same rate

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Magnetic QW layer

- Short MFP
- QW states are spin-dependent

Epitaxial barrier layer (MgO)

- Limited choice of electrodes
- Δ_1 state dominates tunneling



Quantum well states in Fe have Δ_1 symmetry





s-partial DOS at k_{//}=0 for Fe film in Fe/MgO/FeO/8Fe/Cr

5 QW states in majority channel

1 QW state and a resonance in minority channel





Energy and number of nodes of QW states



- Nearly perfect agreement with experiment in positions and thickness dependence
- Resonances from Γ-bar rather than X-bar as earlier speculated
- Different positions for even and odd layers – experimental data averaged over both



I-V Curves



- Tunnel current jumps by 1 to 2 orders of magnitude at resonances
- Larger effect at positive biases
- Majority current flat between resonances all current flows through QW states



TMR



- Large negative TMR at small bias
- Large positive TMR from QW resonances
- TMR negative again at minority spin QW resonance





Conclusions

- Large resonant tunneling through metallic QW states predicted in Fe/MgO/FeO/Fe/Cr and Co/MgO/Fe/Cr
- Tunneling current from QW states above Fermi energy (positvie bias) much greater than from QW states below Fermi energy
- Majority spin QW states contribute to a large positive TMR, minority spin QW states contribute to a large negative TMR
- Due to long MFP of minority spin electrons, resonant tunneling through minority spin QW states may be easier to observe, but requires larger bias windows and thicker films

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